

depletion-type n-channel dual gate MOSFET

designed for . . .



Performance Curves MCB
See Section 4

- VHF Amplifiers
- IF Amplifiers
- Mixers

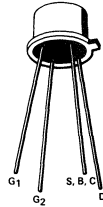
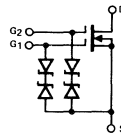
*ABSOLUTE MAXIMUM RATINGS (25°C)

Drain-to-Gate Voltage	20 V
Gate Current, Forward & Reverse	1 mA
Drain-to-Source Voltage	20 V
Drain Current, Continuous	50 mA
Device Dissipation at T _{CASE} = 25°C	1.2 W
Device Dissipation at T _A = 25°C	330 mW
Free Air Temperature above 25°C derate linearly	2.2 mW/°C
Storage Temperature Range	-65 to +200°C
Lead Temperature 1/16" From Case for 10 Seconds	300°C

BENEFITS

- High Gain
g_{fs} Typically 12 mmhos
- No Neutralization Required
Low C_{rss} < 0.03 pF
- Automatic Gain Control with Second Gate

TO-72
See Section 5



*ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

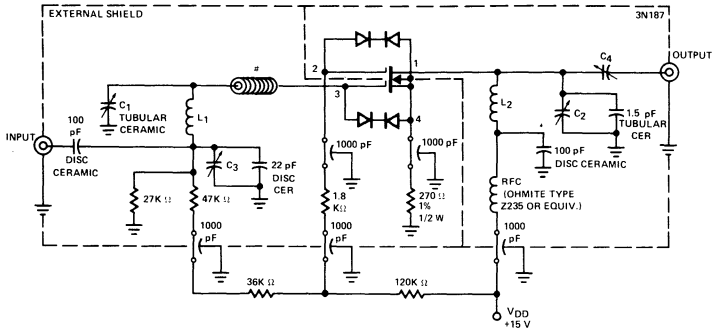
		Characteristic				Test Conditions		
		Min	Typ	Max	Unit			
S T A T I C	1	I _{G1SS}	Gate One to Source Leakage Current			±50	nA	V _{G1S} = ±6 V, V _{G2S} = V _{DS} = 0
	2	I _{G2SS}	Gate Two to Source Leakage Current			±50	nA	V _{G2S} = ±6 V, V _{G1S} = V _{DS} = 0
	3	I _{G1SS}	Gate One to Source Leakage Current			+5	μA	V _{G1S} = ±6 V, V _{G2S} = V _{DS} = 0
	4	I _{G2SS}	Gate Two to Source Leakage Current			+5	μA	V _{G2S} = ±6 V, V _{G1S} = V _{DS} = 0
D Y N A M I C	5	BV _{G1SS}	Gate One to Source Breakdown Voltage	±6.5		+13	V	I _{G1} = ±100 μA, V _{G2S} = V _{DS} = 0
	6	BV _{G2SS}	Gate Two to Source Breakdown Voltage	±6.5		+13	V	I _{G2} = ±100 μA, V _{G1S} = V _{DS} = 0
	7	V _{G1S(off)}	Gate One to Source Cutoff Voltage	-5		-4	V	V _{DS} = 15 V, V _{G2S} = 4 V, I _D = 50 μA
	8	V _{G2S(off)}	Gate Two to Source Cutoff Voltage	-5		-4	V	V _{DS} = 15 V, V _{G1S} = 0, I _D = 50 μA
9	I _{DS}	Zero Gate One Voltage Drain Current	5	15	30	mA	V _{DS} = 15 V, V _{G2S} = 4 V, V _{G1S} = 0	
10	g _{fs}	Common Source Forward Transconductance (Note 1)		7	18	mmho	V _{DS} = 15 V, V _{G2S} = 4 V, I _D = 10 mA	f = 1 kHz
11	C _{iSS}	Common Source Input Capacitance		6	8.5	pF	V _{DS} = 15 V, V _{G2S} = 4 V, I _D = 10 mA	f = 1 MHz
12	C _{rSS}	Common Source Reverse Transfer Capacitance		.02	.03	pF		
13	C _{oss}	Common Source Output Capacitance		2.5		pF		
14	G _{ps}	Common Source Power Gain (Note 2)		16	22	dB	V _{DD} = 15 V, V _{G2S} = 4 V, I _D = 10 mA	f = 200 MHz
15	NF	Noise Figure (Note 2)			4.5	dB		f = 450 MHz
16	G _{ps}	Common Source Power Gain (Notes 3 and 4)		12		dB		f = 450 MHz
17	NF	Noise Figure (Notes 3 and 4)			5.5	dB		f = 450 MHz

* JEDEC registered data

NOTES:

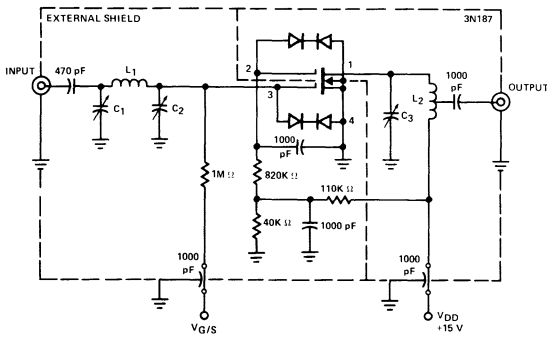
1. Pulse test pulsewidth = 300 μs, duty cycle < 3%.
2. See Figure 1.
3. See Figure 2.
4. Non-JEDEC registered data.

MCB



200 MHz Power Gain and Noise Figure Test Circuit
Figure 1

- C₁ - 1.8 - 8.7 pF variable air capacitor; E.F. Johnson Type 160 104, or equivalent.
- C₂ - 1.5 - 5 pF variable air capacitor; E.F. Johnson Type 160 102, or equivalent.
- C₃ - 1 - 10 pF piston-type variable air capacitor; JFD Type VAM 010; Johnson Type 4335, or equivalent.
- C₄ - 0.8 - 4.5 pF piston type variable air capacitor; Erie 560.013 or equivalent.
- L₁ - 4 turns silver plated 0.02-in. thick, 0.075-0.085-in. wide, copper ribbon. Internal diameter of winding = 0.25 in., winding length approx. 0.08 in.
- L₂ - 4 1/2 turns silver-plated 0.02-in. thick, 0.085-0.095-in. wide, 5/16-in. ID. Coil + 90 in. long.
- 4 - Ferrite bead (4); Pyroferroc Co. "Carbonyl J" 0.09 in. OD, 0.03 in. ID; 0.063 in. thickness.



450 MHz Power Gain and Noise Figure Test Circuit
Figure 2

- C₁ - 2 - 20 pF piston-type variable air capacitor; E.F. Johnson Type MVM 020.
- C₂ - 1 - 10 pF piston-type variable air capacitor; E.F. Johnson Type VAM-010; Johnson Type 4335.
- C₃ - 1 - 10 pF piston-type variable air capacitor; E.F. Johnson Type VAM-010; Johnson Type 4335.
- L₁ - 1/2 turns No. 18 AWG.
- L₂ - 1" No. 16 AWG tapped 1/4" from cold end.